

N-Channel 68 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^d	Q_g (Typ.)
68	0.0018 at $V_{GS} = 10$ V	230	260
	0.0031 at $V_{GS} = 4.5$ V	180	

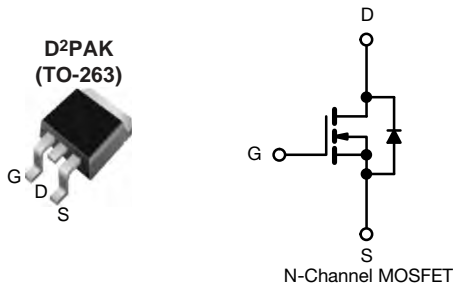
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Power Supply
 - Secondary Synchronous Rectification
- DC/DC Converter



ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	68	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C 230 ^d	A
		$T_C = 70$ °C 180 ^d	
Pulsed Drain Current	I_{DM}	750	
Avalanche Current	I_{AS}	90	
Single Avalanche Energy ^a	E_{AS}	500	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C 285 ^b	W
		$T_A = 25$ °C ^c 9.0	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) ^c	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	1	

Notes:

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).
- Package limited.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{DS} = 0 V, I _D = 250 μA	68			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1		3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 250	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 55 V, V _{GS} = 0 V			1	μA
		V _{DS} = 55 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 55 V, V _{GS} = 0 V, T _J = 150 °C			250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	230			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 22 A		0.0018	0.0022	Ω
		V _{GS} = 4.5 V, I _D = 20 A		0.0031	0.0038	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 20 A		19		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 20 V, f = 1 MHz		9286		pF
Output Capacitance	C _{oss}			2205		
Reverse Transfer Capacitance	C _{rss}			323		
Total Gate Charge ^c	Q _g	V _{DS} = 20 V, V _{GS} = 10 V, I _D = 20 A		99	260	nC
Gate-Source Charge ^c	Q _{gs}			15.3		
Gate-Drain Charge ^c	Q _{gd}			35		
Gate Resistance	R _g	f = 1 MHz	0.5	2.2	5.2	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 20 V, R _L = 2 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω		11	20	ns
Rise Time ^c	t _r			7	14	
Turn-Off Delay Time ^c	t _{d(off)}			45	68	
Fall Time ^c	t _f			7	14	
Drain-Source Body Diode Ratings and Characteristics T _C = 25 °C ^b						
Continuous Current	I _S				230	A
Pulsed Current	I _{SM}				750	
Forward Voltage ^a	V _{SD}	I _F = 10 A, V _{GS} = 0 V		0.72	1.2	V
Reverse Recovery Time	t _{rr}	I _F = 10 A, dI/dt = 100 A/μs		42	63	ns
Peak Reverse Recovery Current	I _{RM(REC)}			2.9	4.8	A
Reverse Recovery Charge	Q _{rr}				52	78

Notes:

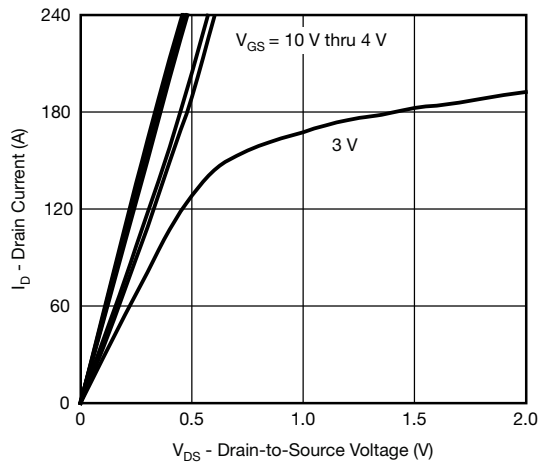
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

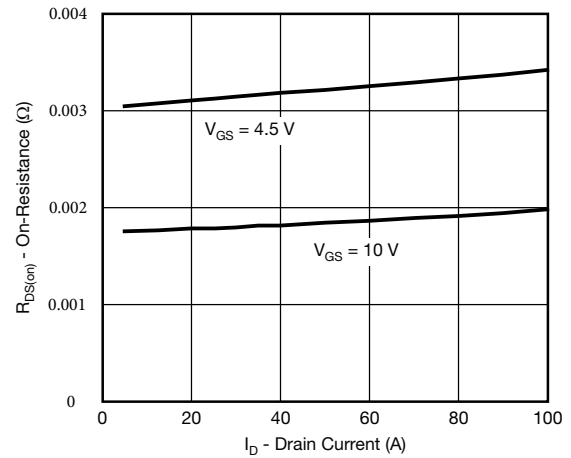
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

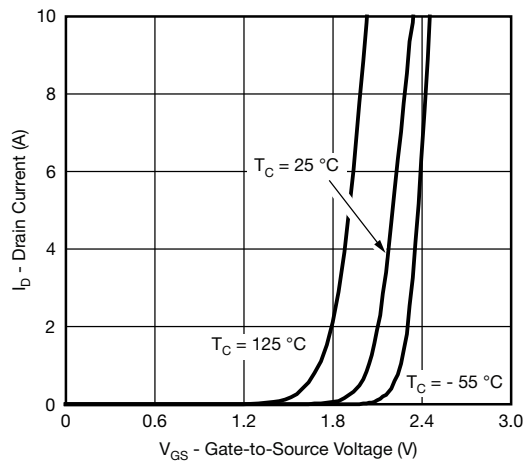
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



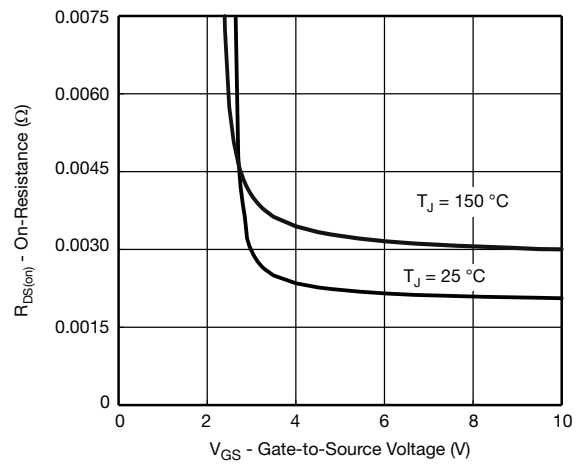
Output Characteristics



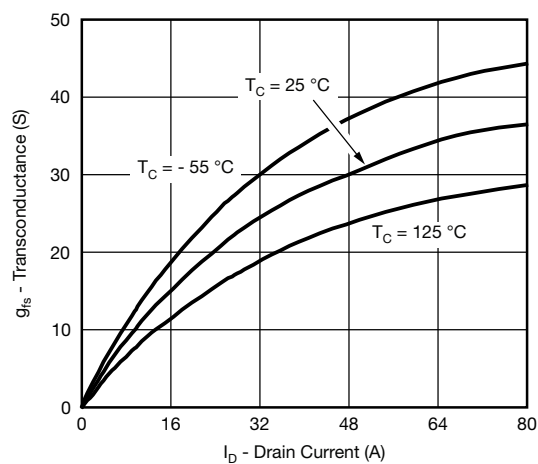
On-Resistance vs. Drain Current



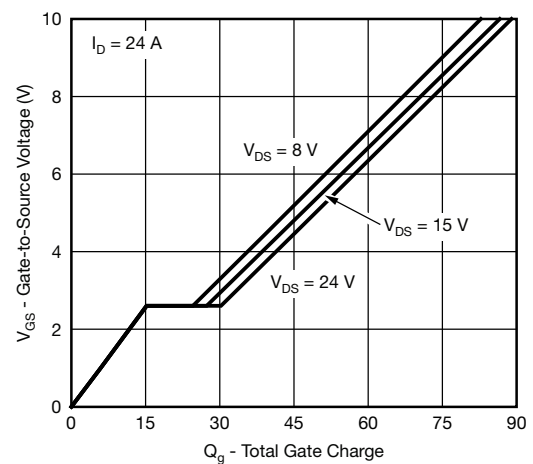
Transfer Characteristics



On-Resistance vs. Gate-to-Source Voltage

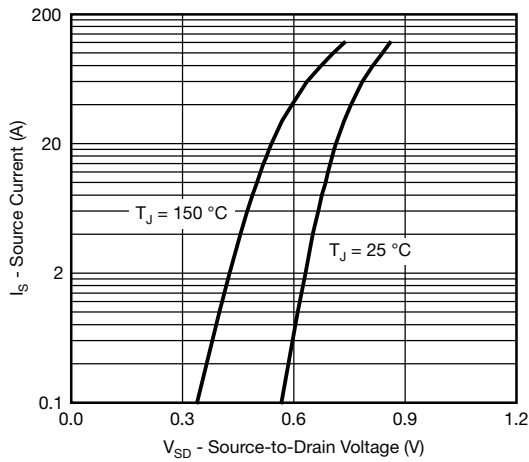


Transconductance

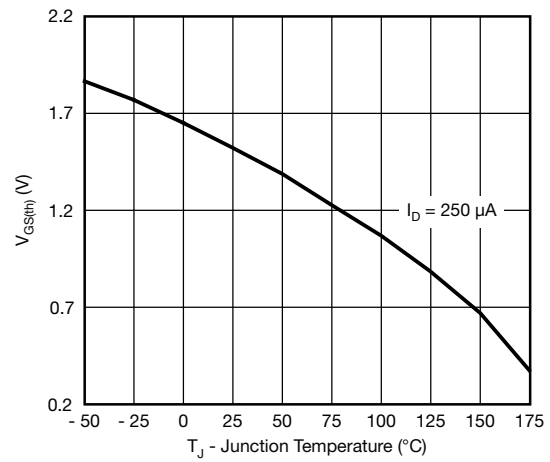


Gate Charge

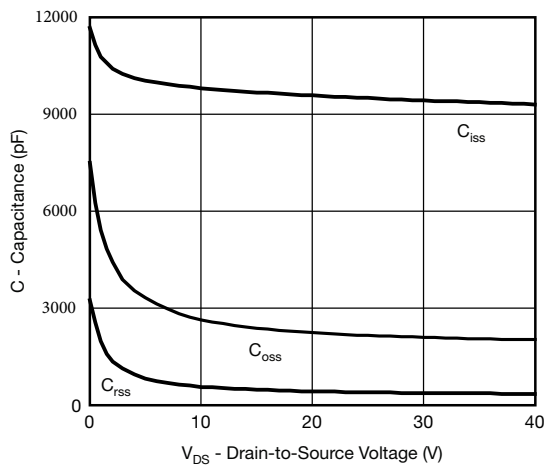
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



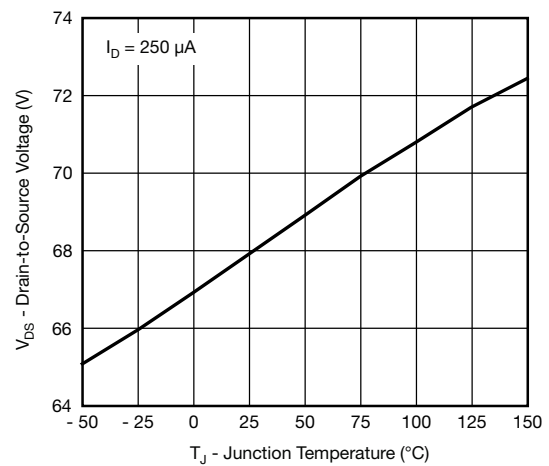
Source-Drain Diode Forward Voltage



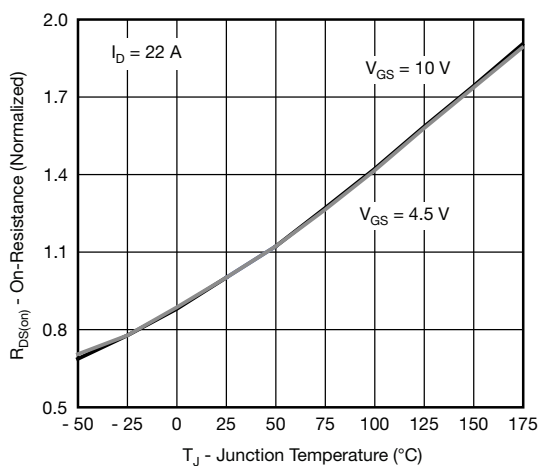
Threshold Voltage



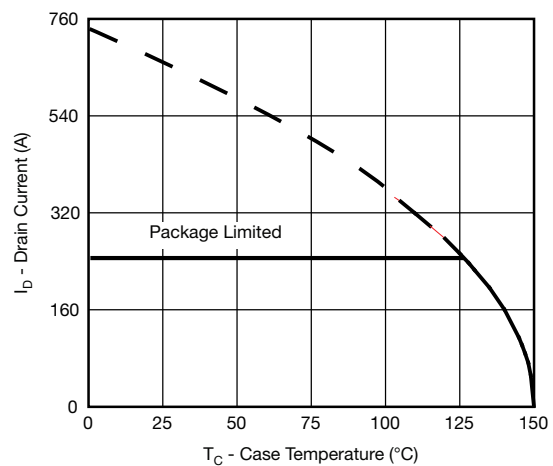
Capacitance



Drain Source Breakdown vs. Junction Temperature

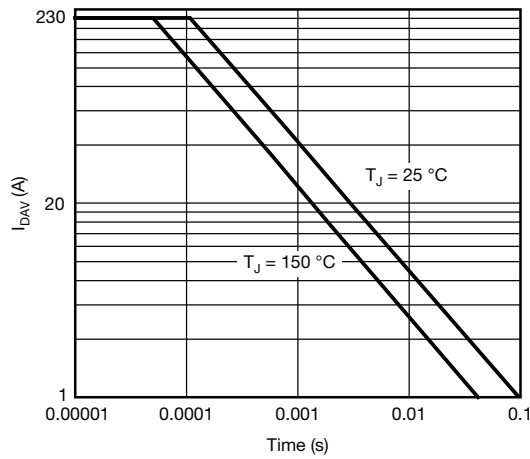


On-Resistance vs. Junction Temperature

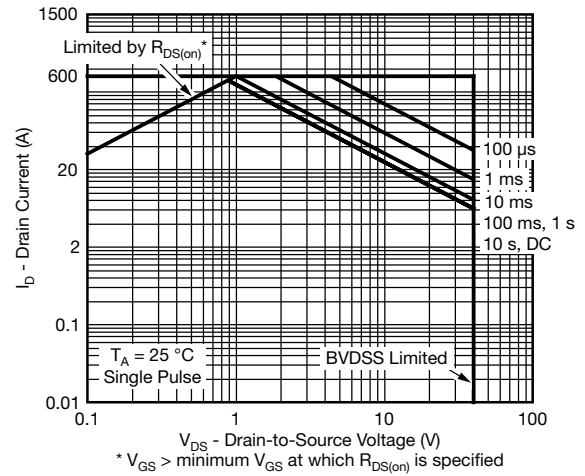


Current Derating

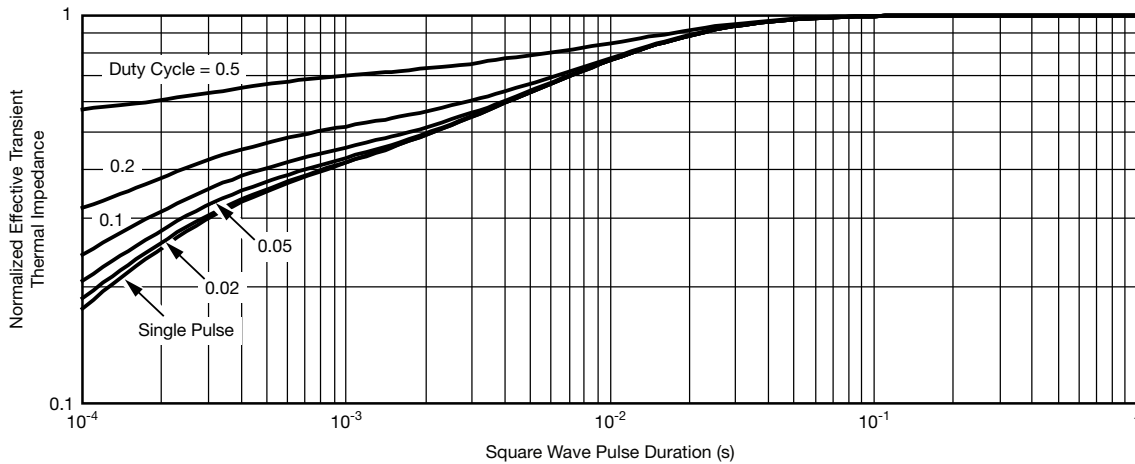
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Single Pulse Avalanche Current Capability vs. Time



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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